

NEWS RELEASE



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FOR IMMEDIATE RELEASE

Peregrine Semiconductor Extends 3G Handset Switch Offering

PE42671 UltraCMOS™ SP7T RF Switch Features Four TX Paths

San Diego, California, January 16, 2006 -- Peregrine Semiconductor Corporation, a supplier of the industry's most advanced RF CMOS and mixed-signal communications ICs, today unveiled the PE42671 SP7T Cellular Handset Switch at the IEEE Microwave Theory and Technique (MTT) Society's *Radio & Wireless Symposium* held in San Diego. This new device complements the SP6T and SP7T RF ICs launched last quarter from the Company's next-generation UltraCMOS process with HaRP™ technology enhancements. The newest device addresses the specific design requirements of next-generation dual-mode WCDMA handsets.

The PE42671 is the industry's only monolithic 3GPP IMD-compliant SP7T device capable of dual-band WCDMA and GSM requirements. Additionally, the switch offers the industry's most flexible combination of communication paths: two transmit ports that can be used for GSM/PCS/EDGE, two transmit/receive ports that can be used for either WCDMA or as receive ports, and three symmetric receive ports. This unique design allows engineering flexibility and ease-of-development not currently available in the high-throw RF switch arena. Like its predecessors, the PE42671 is a highly integrated solution that simplifies and lowers the cost of RF designs by reducing overall part count in an ASM by as many as 6 devices and 13 wire bonds.

PE42671 is also the world's most linear and usable SP7T switch with its exceptional harmonic performance ($2f_0 = -88$ dBc and $3f_0 = -80$ dBc) IP3 of +68 dBm; world-class 1.5 KV ESD tolerance; 2.75 V operating voltage and ultra-low power consumption.

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“The UltraCMOS switch product line is proof positive that the turning point is now,” stated Jim Cable, CEO of Peregrine Semiconductor. “To bring to market a monolithic SP7T RF switch with 4 TX ports and an IP3 of +68 dBm on CMOS is an outstanding accomplishment. Yet even more extraordinary is the global acceptance of ASM, FEM and transmit module manufacturers, and how UltraCMOS has become the enabling technology upon which future RF project roadmaps are being designed. It’s truly time to switch,” he added.

The PE42671 continues in Peregrine’s tradition of delivering world-class RF performance: TX-RX Isolation of +47 dB at 900 MHz and +40 dB at 1900 MHz; P1dB compression point of +41 dBm; and 0.65 dB of insertion loss at 900 MHz. On-chip CMOS decode logic facilitates both 1.8 V and 2.75 V three-pin CMOS control inputs, while no blocking capacitors and on-chip SAW filter over-voltage protection devices ensure ease-of-integration.

The PE42671 die is priced at \$0.75 ea. (25K units) Orders are being taken for the devices which are available in die form and sampling to select customers directly from Peregrine.

About UltraCMOS™ Technology and the HaRP™ Invention

UltraCMOS™ mixed-signal process technology is a patented variation of silicon-on-insulator (SOI) technology using a sapphire substrate, providing high yields and competitive costs. This technology delivers significant performance advantages over competing processes such as GaAs, SiGe BiCMOS and bulk silicon CMOS in applications where RF performance, low power and integration are paramount. The HaRP technology inventions are patented process and design advancements which dramatically improve harmonic results, linearity and overall RF performance -- specifications required by the 3GPP standards body for GSM/WCDMA applications, and today unmatched in the industry. In particular, long-awaited triumphs in Intermodulation Distortion (IMD) are now available to multi-band front-end module and handset manufacturers alike. Peregrine’s newest cellular handset switches provide for an ever-increasing number of RF paths to connect to the antenna through a single CMOS device. [Learn more.](#)

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ADD TWO/PE42671

About Peregrine Semiconductor

Peregrine Semiconductor Corporation designs, manufactures, and markets high-performance communications ICs for the wireless infrastructure and mobile wireless; broadband communications; space, defense and avionics markets. Manufactured on the Company's proprietary UltraCMOS™ mixed-signal process technology, Peregrine products are uniquely poised to meet the needs of a global RF design community in high-growth applications such as WCDMA and GSM digital cellular, broadband, DTV, DVR and rad-hard space and defense programs. Peregrine 0.25µm and 0.5µm UltraCMOS devices are manufactured in its 6" CMOS facility located in Sydney, Australia and in Hachioji, Japan through an alliance with OKI Electric Industry Co., Ltd. The Company, headquartered in San Diego, California, maintains global sales support operations and a worldwide technical distribution network. Additional information is available on the web at psemi.com. Contact Peregrine's worldwide distribution partner, Richardson Electronics for sales information at www.rell.com or 1-800-737-6937.

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